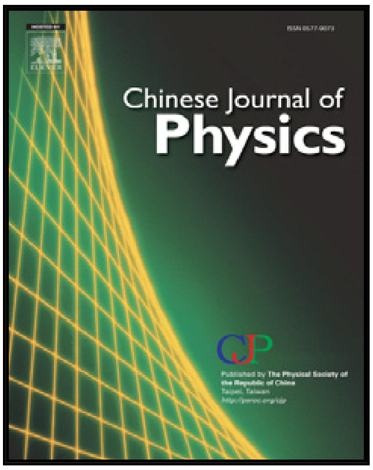

Effect of the built-in electric field on electron Raman scattering of parabolic $In_xGa_{1-x}N/GaN$ quantum dot

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Highlights

- Raman spectra is proposed for InxGa1-xN/GaN quantum dot with effective mass approach.
- Various built-in electric field accounts for energy shift of the spectrum.
- As built-in electric field increases, FWHM of spectrum decreases.